

## 60V N-Channel MOSFET



**TO-92** 

# **5**

#### **Pin Definition:**

- 1. Source
- 2. Gate
- 3. Drain

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (mA)		
60	5 @ V <sub>GS</sub> = 10V	100		
	5.5 @ V <sub>GS</sub> = 5V	100		

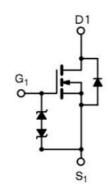
#### **Features**

- Low On-Resistance
- ESD Protection
- High Speed Switching
- Low Voltage Drive

### **Ordering Information**

Part No.	Package	Packing
TSM2N7000KCT B0	TO-92	1Kpcs / Bulk
TSM2N7000KCT A3	TO-92	2Kpcs / Ammo

#### **Block Diagram**



N-Channel MOSFET

#### **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	60	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Drain Current	Continuous @ T <sub>A</sub> =25°C	I <sub>D</sub>	300	mA	
	Pulsed	I <sub>DM</sub>	700		
Drain Reverse Current	Continuous @ T <sub>A</sub> =25°C	I <sub>DR</sub>	300	mA	
	Pulsed	I <sub>DMR</sub>	700		
Maximum Power Dissipation		$P_{D}$	400	mW	
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		$T_J, T_STG$	-55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	$T_L$	10	S
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	357	°C/W

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.



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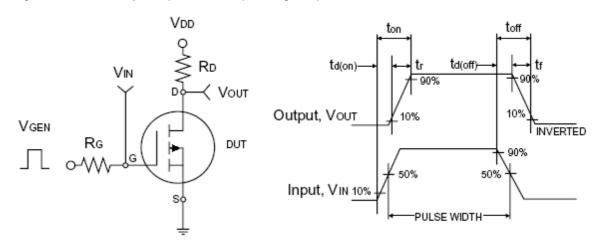


**Electrical Specifications** (Ta = 25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 10\mu A$	BV <sub>DSS</sub>	60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	1.0		2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±10	uA
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	uA
Danier Courses On Otata Desistance	$V_{GS} = 10V, I_D = 100mA$	Б		3	5	
Drain-Source On-State Resistance $V_{GS} = 5V, I_D = 100mA$ $R_{DS(ON)}$		3.6	5.5	Ω		
Forward Transconductance	$V_{DS} = 10V, I_{D} = 200mA$	g <sub>fs</sub>	100			mS
Diode Forward Voltage	$I_S = 300 \text{mA}, V_{GS} = 0 \text{V}$	V <sub>SD</sub>		0.9	1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	$V_{DS} = 10V, I_D = 250mA,$ $V_{GS} = 4.5V$	$Q_g$		0.4		nC
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C <sub>iss</sub>		7.32		
Output Capacitance		C <sub>oss</sub>		3.42		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		7.63		
Switching <sup>c</sup>						
Turn-On Delay Time	$V_{DD} = 30V, R_{G} = 10\Omega$	t <sub>d(on)</sub>		25		C
Turn-Off Delay Time	$I_D = 100 \text{mA}, V_{GEN} = 10 \text{V},$	t <sub>d(off)</sub>		35		nS

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
  b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

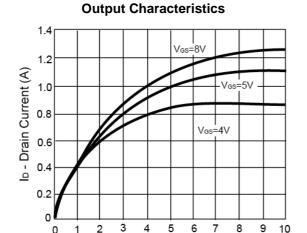
Switchin Waveforms



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#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



## 1.4 1.2 lo - Drain Current (A) 1.0 0.8 0.6 0.4 0.2

**Transfer Characteristics** 

#### **On-Resistance vs. Drain Current**

4

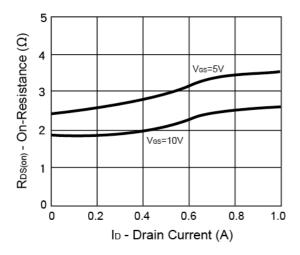
6 7 8

VDS - Drain-to-Source Voltage (V)

10

2

0



#### Forward Transfer Admittance vs. Drain Current

5

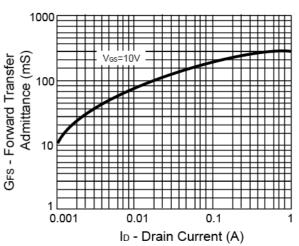
V<sub>GS</sub> - Gate-to-Source Voltage (V)

6 7 8 9 10

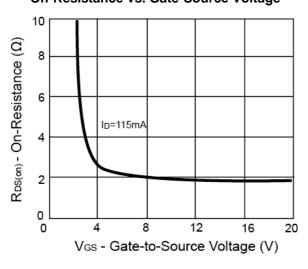
0

0

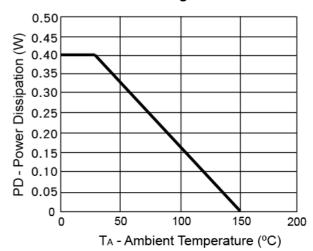
2 3 4



#### On-Resistance vs. Gate-Source Voltage



#### **Power Derating Curve**

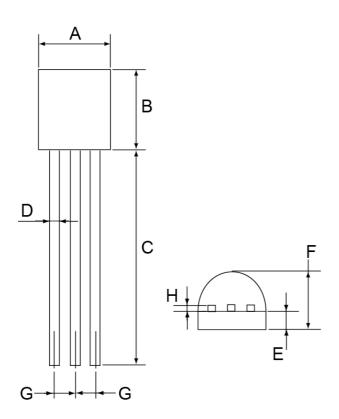








## **TO-92 Mechanical Drawing**



TO-92 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	4.30	4.70	0.169	0.185	
В	4.30	4.70	0.169	0.185	
С	13.53 (typ)		0.532 (typ)		
D	0.39	0.49	0.015	0.019	
Е	1.18	1.28	0.046	0.050	
F	3.30	3.70	0.130	0.146	
G	1.27	1.31	0.050	0.051	
Н	0.33	0.43	0.013	0.017	

## **Marking Diagram**



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

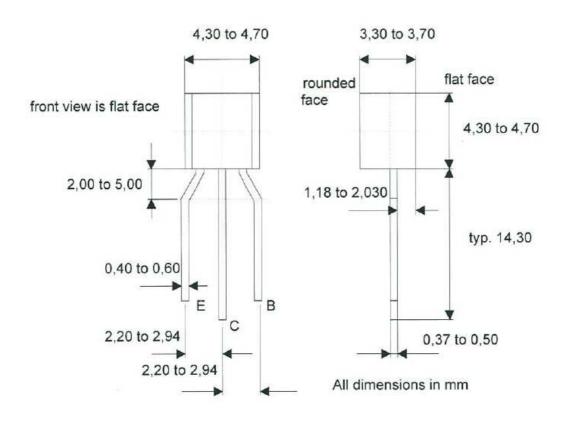
L = Lot Code



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## **TO-92 Ammo Pack Mechanical Drawing**





## TSM2N7000K 60V N-Channel MOSFET

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